

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
TOPTICS.018AAPPLICATION NO.
09/891,689INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Gene H. HaertlingFILING DATE
June 26, 2001GROUP
2873

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
<i>E.H.</i>	6,288,822	09/11/01	Romanovsky	359	245	
<i>E.H.</i>	6,297,899	10/02/01	Romanovsky	359	245	
<i>E.H.</i>	6,486,996	11/26/02	Romanovsky	359	245	
<i>E.H.</i>	6,614,574	09/02/03	Romanovsky	359	247	
<i>E.H.</i>	2002/0181067	12/05/02	Romanovsky, et al. (SN 10/013 336)	359	245	

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

EXAMINER
INITIAL

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

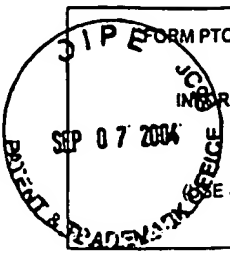
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EXAMINER

DATE CONSIDERED

4-13-05

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	FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. TOPTICS.018A	APPLICATION NO. 09/891,689
	INFORMATION DISCLOSURE STATEMENT BY APPLICANT			
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FILING DATE June 26, 2001			GROUP 2873	

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
<i>EAH</i>	1.	4,201,442	05/1980	McMahon et al.	385	17	
<i>EAH</i>	2.	4,796,982	01/1989	Kitabatake et al.	359	318	
<i>EAH</i>	3.	4,993,811	02/1991	Blazey et al.	359	251	
<i>EAH</i>	4.	5,011,271	04/30/91	Saito et al.	359	359	
<i>EAH</i>	5.	5,016,959	05/1991	Diemeer	385	16	
<i>EAH</i>	6.	5,745,280	4/1998	Kitano	359	290	
<i>EAH</i>	7.	5,369,718	11/1994	Kamata et al.	385	21	
<i>EAH</i>	8.	5,911,018	6/1999	Bischel et al.	385	16	

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
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<i>EAH</i>	9.	0 344 857 A1	05/1989	Europe				

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

EXAMINER INITIAL		OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
<i>EAH</i>	10.	Antiferroelectric-Phase PLZT For Use In High Density Optical Data Storage, S. Mancha, J. Bullington, R. Carter and C. Dehainaut, Airforce Weapons Laboratory (AFSC) Kirtland Airforce Base New Mexico, <i>Ferroelectrics</i> , 1988 Gordon and Breach Science Publishers S.A., Vol. 82, pp. 99-104.
<i>EAH</i>	11.	Crystallization of Lanthanum-Modified Lead Zirconate Titanate (PLZT) Using Coprecipitated Gels, Yao-Jung Lee, Fu-Su Yen, Jong-Ping Wu and Hsing-I Hsiang, Jpn. J. Appl. Phys., Vol. 34, Pt. 1, No. 8A, August 1995, pp. 4137-4142.
<i>EAH</i>	12.	Crystallization of Silicon on Electro-Optic PLZT by a Laser Beam Modulated in Shape and Intensity Profile, T.H. Lin, M.L. Burgener, S.C. Esener and S.H. Lee, Mat. Res. Soc. Symp. Proc., Vol. 74, 1987, pp. 135-140.
<i>EAH</i>	13.	Dielectric Properties of (111) and (100) Lead-Zirconate-Titanate Films Prepared by Sol-Gel Technique, K. Aoki et al., Jpn. J. Appl. Phys., Vol. 33, (1994) Pt. 1, No. 9B, pp. 5155-5158.
<i>EAH</i>	14.	Effects of O3 on Growth and Electrical Properties of Pb(Zr, Ti)O3 Thin Films by Photoenhanced Metalorganic Chemical Vapor Deposition, Masaru Shimizu et al., Jpn. J. Appl. Phys., Vol. 33, (1994) Pt. 1, No. 9B, pp. 5135-5138.
<i>EAH</i>	15.	Electric and Optical Properties of PLZT Ceramic Shutter Array, Y. Takubo et al., Jpn. J. Appl. Phys., Vol. 24 (1985) Supplement 24-3, pp. 159-161.
<i>EAH</i>	16.	Fabrication of Transparent PLZT Ceramics by Atmosphere Sintering, Katsuhiko Tanaka et al., Japanese Journal of Applied Physics, Vol. 24 (1985) Supplement 26-3, pp. 107-109.
<i>EAH</i>	17.	Fabrication of Transparent PLZT Ceramics with a High Transmittance and Their Application to Optical Light Shutter, Kunihiro Hayashi, et al., Proceedings of the 6th Meeting on Ferroelectric Materials and Their Applications, Kyoto 1987, Japanese Journal of Applied Physics, Vol. 26 (1987) Supplement 26-2, pp. 126-128.
<i>EAH</i>	18.	High Speed Optical TIR Switches Using PLZT Thin-Film Waveguides on Sapphire, Hidetaka Higashino, Takao Kawaguchi, Hideaki Adachi, Toshihiko Makino and Osamu Yamazaki, Proceedings of the Sixth International meeting on Ferroelectricity, Kobe, 1985, Jpn. J. Appl. Phys. Vol 24 (1985) Suppl. 24-2, p. 284-286.

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<i>EAH</i>	19. Optical Switch Utilizing Total Reflection of (Pb, La) (Zr, Ti)O ₃ Ceramics, Toshio Utsunomiya, Jpn J. Appl. Phys. Vol. 33 (1994) pp. 5440-5442 Part 1, No. 9B, September 1994.
<i>EAH</i>	20. Optical TIR Switches Using PLZT-Thin-Film Waveguides on Sapphire, Kiyotaka Wasa et al., Journal of Lightwave Technology, Vol. LT-2, No. 5, pp. 710-713, October 1984.
<i>EAH</i>	21. A (Pb, La)(Zr, Ti)O ₃ (PLZT) Polarization-Plane with a Buried Electrode Structure for a Mid-Infrared Electro-Optical Shutter, Yoshiharu Taniguchi, Kensuke Murakami, Hiroshi Kobayashi and Shosaku Tanaka, Jpn. J. Appl. Phys., Vol. 36 (1997) Pt. 1, No. 5A, pp. 2709-2714.
<i>EAH</i>	22. PLZT Electrooptic Shutter, K. Tanaka et al., Jpn. J. Appl. Phys., Vol. 22 (1983) Supplement 22-2, pp. 126-128.
<i>EAH</i>	23. The Polarization-Reversal Characteristics of Pb(Zr, Ti)O ₃ Family Ceramics, Y. Masuda et al., Proceedings of the 4 th Meeting on Ferroelectric Materials and Their Applications, Kyoto 1983/ Jpn. J. Appl. Phys., Vol. 22 (1983) Supplement 22-2, pp. 118-122.
<i>EAH</i>	24. Preparation and Characterization of Sol-Gel Derived Epitaxial and Oriented Pb(Zr _{0.52} Ti _{0.48})O ₃ Thin Films, Keiichi Nashimoto and Shigetoshi Nakamura, Jpn. J. Appl. Phys., Vol. 33 (1994) Pt. 1, No. 9B, pp. 5147-5150.
<i>EAH</i>	25. Preparation of Pb(Zr, Ti)O ₃ Thin Films by Sol-Gel Technique, Tomoyasu Takusagawa, Noriaki Yamada, Terumasa Kato, Hajime Hattori and Teruyuki Matsui, Jpn. J. Appl. Phys. Vol. 33, Pt. 1, No. 9B, 1994, pp. 5151-5154.
<i>EAH</i>	26. Prism-Type Optical Deflector Using PLZT Ceramics, Toshio Utsunomiya et al., Japanese Journal of Applied Physics, Vol. 24, (1985) Supplement 24-3, pp. 169-171.
<i>EAH</i>	27. Uniform Ultra-Thin Pb(Zr, Ti)O ₃ Films Formed by Metal-Organic Chemical Vapor Deposition and Their Electrical Characteristics, Hiroshi Miki and Yuzuru Ohji, Jpn. J. Appl. Phys., Vol. 33 (1994) Pt. 1, No. 9B, pp. 5143-5146.
<i>EAH</i>	28. (Co-pending) U.S. Patent Application No. 40/040,336 (Attorney Docket No. TOPTICS-8846P2) See US PG Pub 2002/0181067 already listed

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